

ABSTRACT OF THE DISCLOSURE

A semiconductor cleaning method, including providing a semiconductor wafer, forming a first layer of oxide over the semiconductor wafer, forming a floating gate layer over the first layer of oxide, forming a second layer of oxide over the floating gate layer, etching the first layer of oxide, the floating gate layer, and the second layer of oxide to form a gate structure, cleaning the semiconductor wafer including the gate structure using an ozonated de-ionized (DI) water, further cleaning of the ozonated water-cleaned semiconductor wafer using a first cleaning solution, and additional cleaning of the further cleaned semiconductor wafer using a second cleaning solution.

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